

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

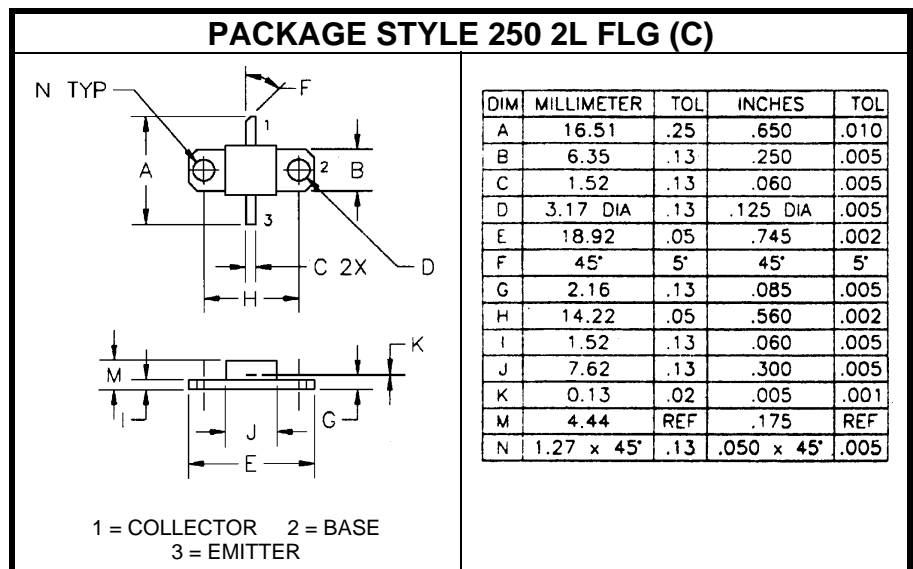
The **ASI MRA1417-11** is a Common Base Device Designed for Class C Power Amplifier Applications up to 1.7 GHz.

FEATURES INCLUDE:

- Gold Metallization
- Emitter Ballasting
- Input Matching

MAXIMUM RATINGS

I_C	4.0 A
V_{CB0}	50 V
P_{DISS}	12 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	4.5 °C/W


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	I _C = 80 mA	50			V
BV_{EBO}	I _E = 1.0 mA	3.5			V
I_{CB0}	V _{CB} = 28 V			2.0	mA
h_{FE}	V _{CE} = 5.0 V I _C = 4.0 A	10		100	---
C_{ob}	V _{CB} = 28 V f = 1.0 MHz			12	pF
P_G	V _{CE} = 28 V P _{OUT} = 11 W f = 1700 MHz	7.4			dB
η_C		45			%